



10N80-CQ

Power MOSFET

10A, 800V N-CHANNEL POWER MOSFET

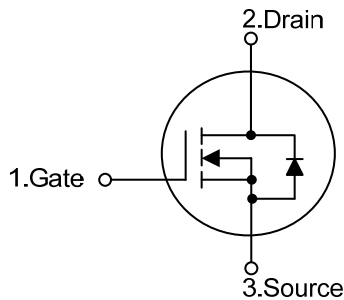
DESCRIPTION

The UTC 10N80-CQ provide excellent $R_{DS(ON)}$, low gate charge and operation with low gate voltages. This device is suitable for use as a load switch or in PWM applications.

FEATURES

- * $R_{DS(ON)} \leq 1.4\Omega$ @ $V_{GS}=10V$, $I_D=5.0A$
- * Low Reverse Transfer Capacitance
- * Fast Switching Capability
- * Avalanche Energy Specified
- * Improved dv/dt Capability, High Ruggedness

SYMBOL



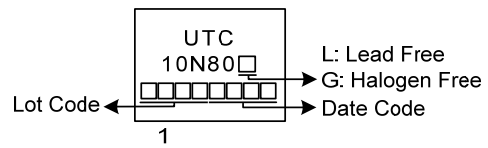
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
10N80L-TA3-T	10N80G-TA3-T	TO-220	G	D	S	Tube
10N80L-TF1-T	10N80G-TF1-T	TO-220F1	G	D	S	Tube
10N80L-TF3-T	10N80G-TF3-T	TO-220F	G	D	S	Tube
10N80L-T2Q-T	10N80G-T2Q-T	TO-262	G	D	S	Tube
10N80L-TQ2-T	10N80G-TQ2-T	TO-263	G	D	S	Tube
10N80L-TQ2-R	10N80G-TQ2-R	TO-263	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

10N80G-TA3-T	(1) T: Tube, R: Tape Reel (2) TA3: TO-220, TF1: TO-220F1, TF3: TO-220F T2Q: TO-262, TQ2: TO-263 (3) G: Halogen Free and Lead Free, L: Lead Free
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■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V _{DSS}	800	V
Gate-Source Voltage		V _{GSS}	±30	V
Drain Current	Continuous	I _D	10	A
	Pulsed (Note 2)	I _{DM}	40	A
Avalanche Energy	Single Pulsed (Note 3)	E _{AS}	168	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	1.5	V/ns
Power Dissipation	TO-220/TO-262	P _D	145	W
	TO-263			
	TO-220F/TO-220F1		30	W
Junction Temperature		T _J	+150	°C
Storage Temperature		T _{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature.

3. L=10mH, I_{AS}=5.8A, V_{DD}=50V, R_G=25 Ω, Starting T_J = 25°C

4. I_{SD}≤10A, di/dt≤200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C

■ THERMAL CHARACTERISTICS

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient		θ _{JA}	62.5	°C/W
Junction to Case	TO-220/TO-262	θ _{JC}	0.86	°C/W
	TO-263			
	TO-220F/TO-220F1		4.2	°C/W

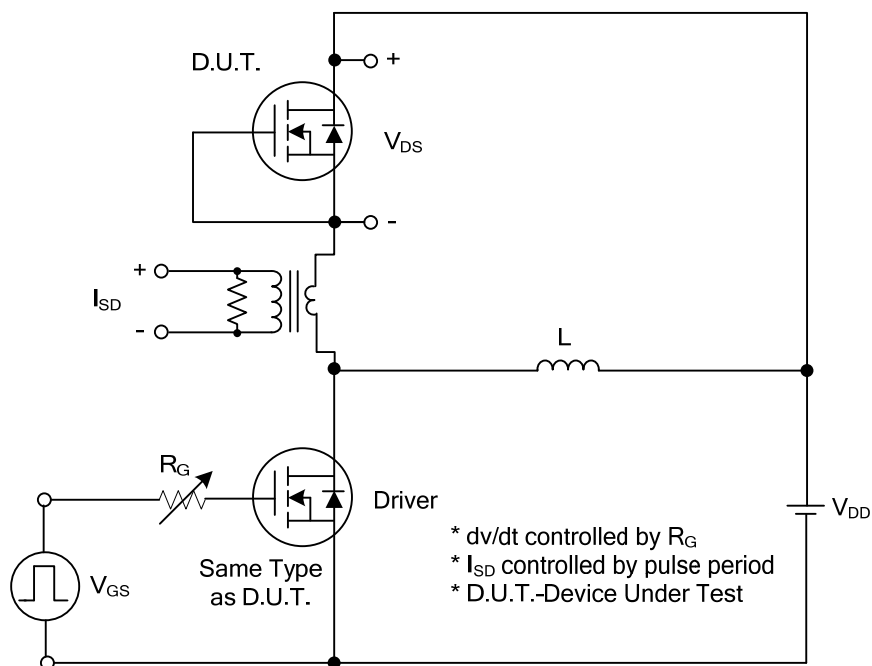
■ **ELECTRICAL CHARACTERISTICS** ($T_J = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	800			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =800V, V _{GS} =0V			10	μA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±30V, V _{DS} =0V			±10	μA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	3.0		5.0	V
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =5.0A		1.25	1.4	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{ISS}	V _{DS} =25V, V _{GS} =0V, f=1MHz		1300		pF
Output Capacitance	C _{OSS}			150		pF
Reverse Transfer Capacitance	C _{RSS}			15		pF
SWITCHING CHARACTERISTICS						
Total Gate Charge (Note 1)	Q _G	V _{DS} =100V, V _{GS} =10V, I _D =10A I _G =1mA (Note 1, 2)		37		nC
Gate-Source Charge	Q _{GS}			8.5		nC
Gate-Drain Charge	Q _{GD}			11		nC
Turn-On Delay Time (Note 1)	t _{D(ON)}	V _{DD} =100V, V _{GS} =10V, I _D =10A, R _G =25Ω (Note 1, 2)		23		ns
Turn-On Rise Time	t _R			21		ns
Turn-Off Delay Time	t _{D(OFF)}			102		ns
Turn-Off Fall Time	t _F			47		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Continuous Drain-Source Diode Forward Current	I _S				10	A
Maximum Pulsed Drain-Source Diode Forward Current	I _{SM}				40	A
Drain-Source Diode Forward Voltage (Note 1)	V _{SD}	I _S =10A, V _{GS} =0V			1.4	V
Body Diode Reverse Recovery Time (Note 1)	t _{rr}	I _S =10A, V _{GS} =0V, dI _F /dt=100A/μs		545		nS
Body Diode Reverse Recovery Charge	Q _{rr}			8		μC

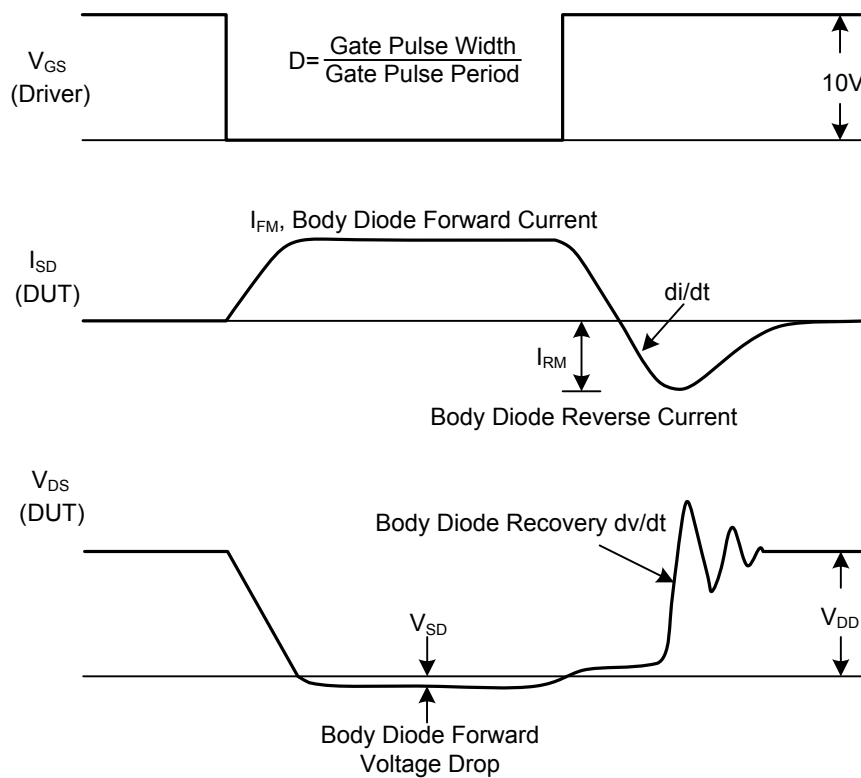
Notes: 1. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

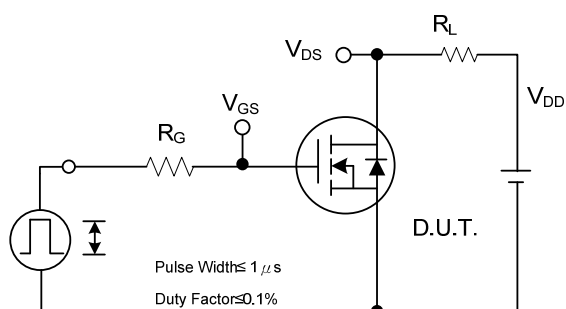


Peak Diode Recovery dv/dt Test Circuit

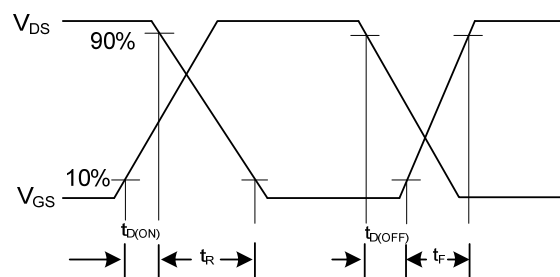


Peak Diode Recovery dv/dt Waveforms

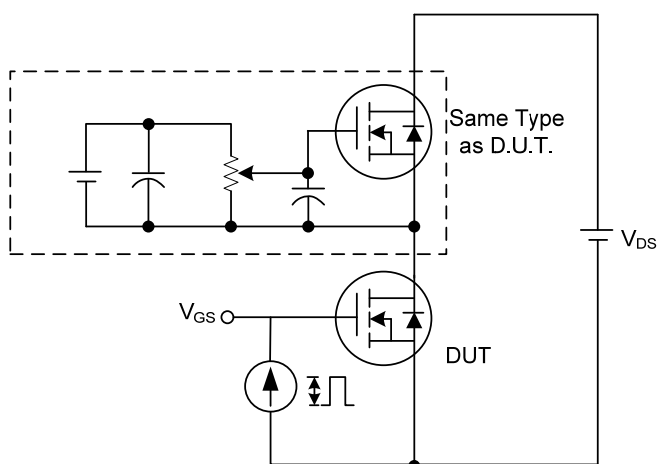
■ TEST CIRCUITS AND WAVEFORMS



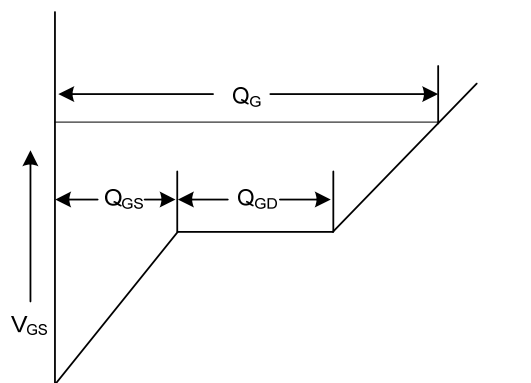
Switching Test Circuit



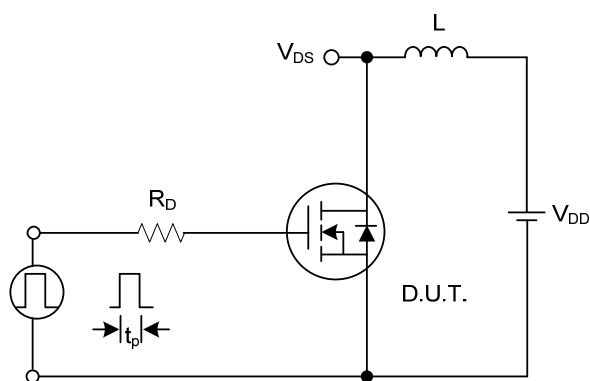
Switching Waveforms



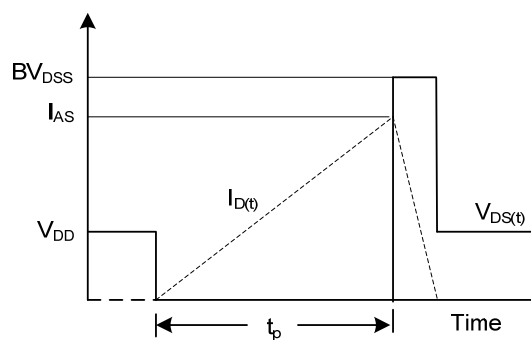
Gate Charge Test Circuit



Charge
Gate Charge Waveform

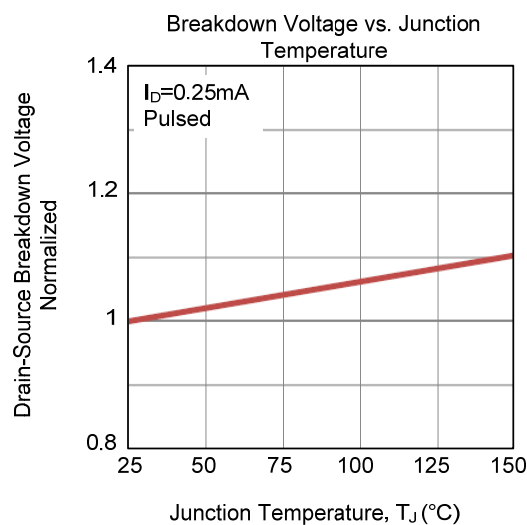
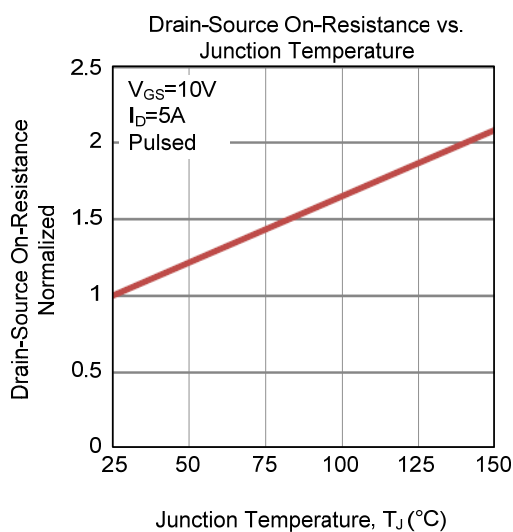
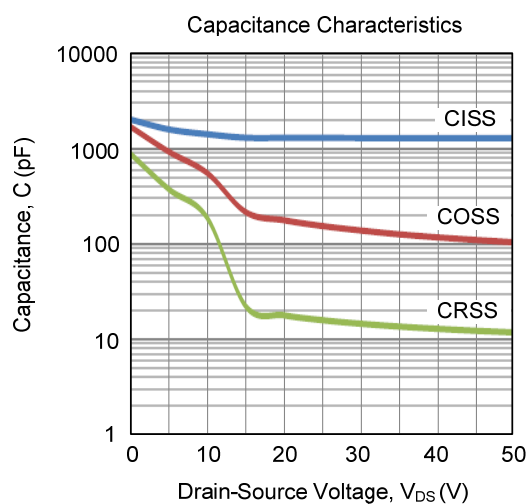
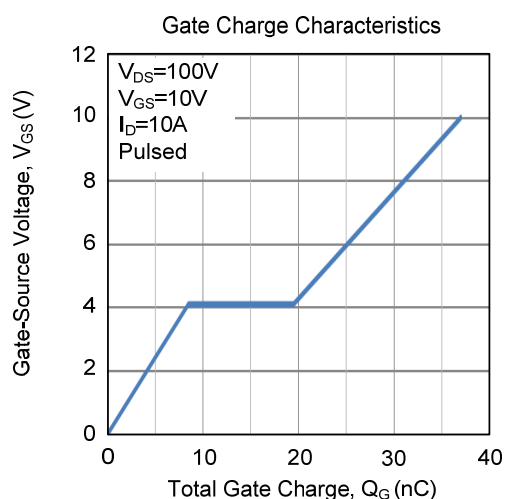
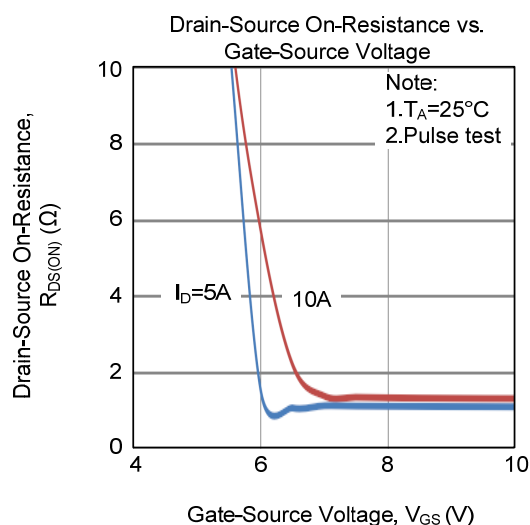
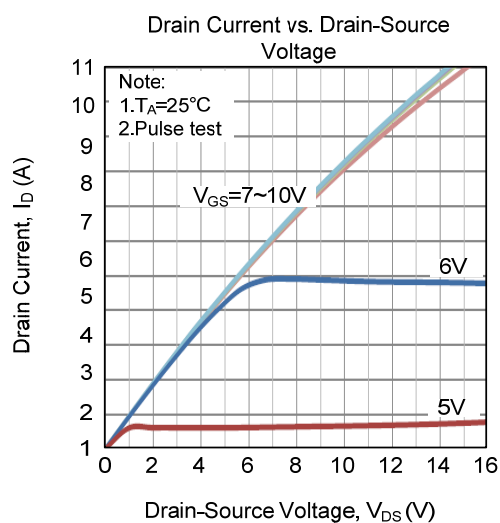


Unclamped Inductive Switching Test Circuit

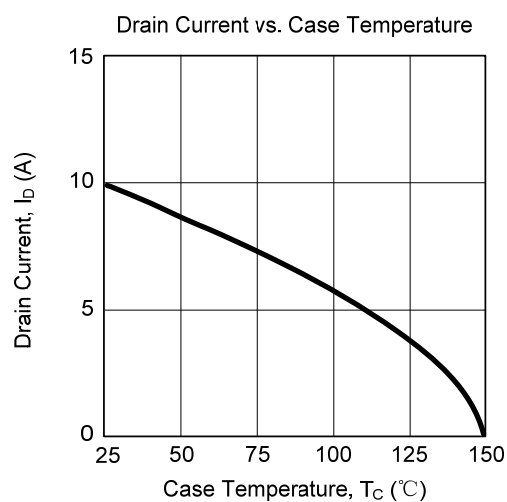
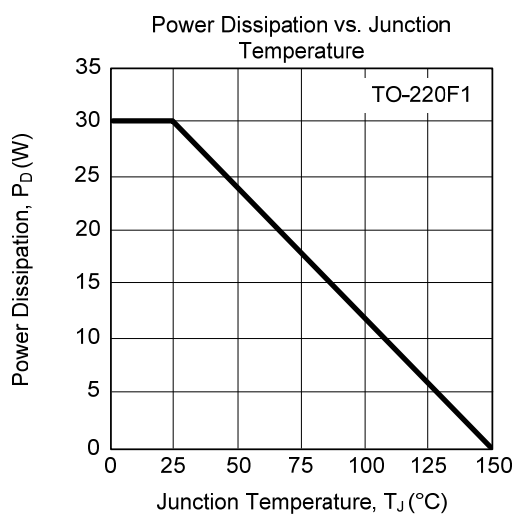
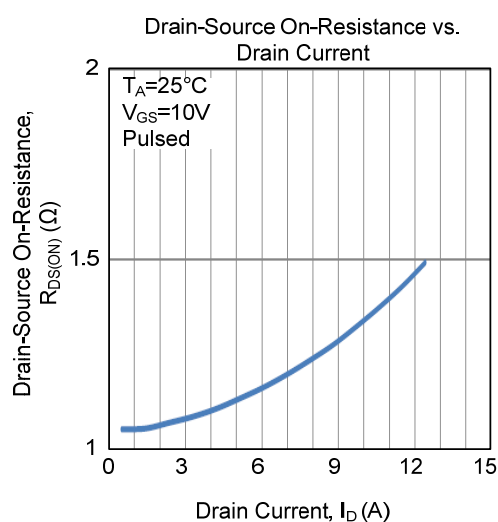
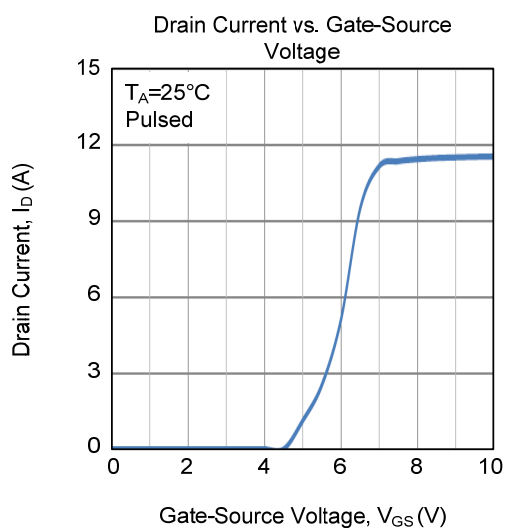
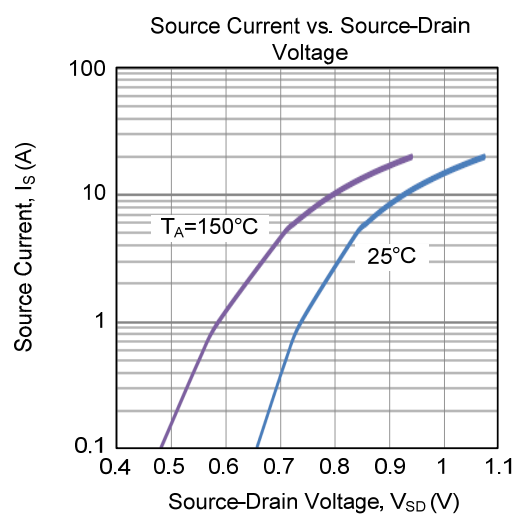
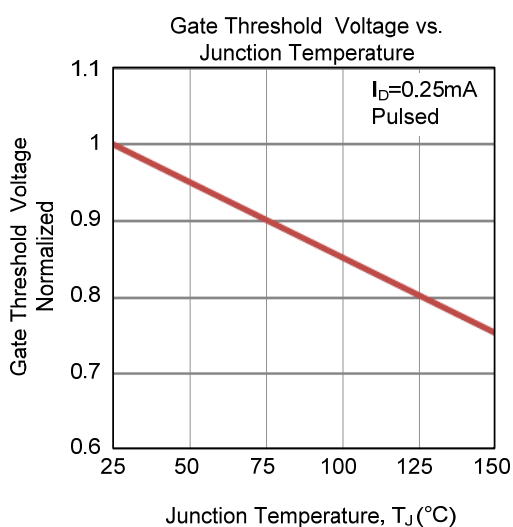


Unclamped Inductive Switching Waveforms

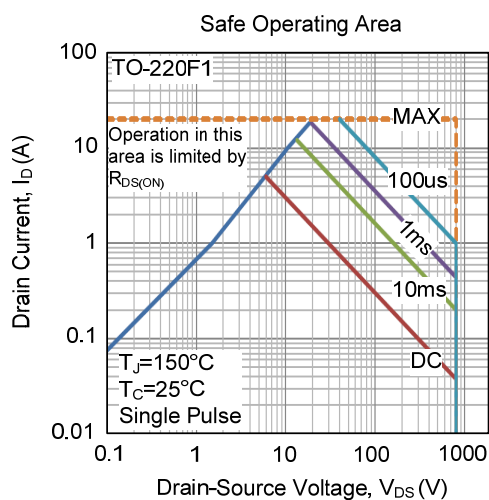
■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



■ TYPICAL CHARACTERISTICS (Cont.)



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